# Theory of M ott insulator/band insulator heterostructure

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A theory of heterostructures comprised of LaTiD<sub>3</sub> (a Mott insulator) and SrTiD<sub>3</sub> (a band insulator) is presented. The band structure of the Tid-electrons is treated with a nearest neighbor tight-binding approximation; the electric elds arising from the La<sup>3+</sup>/Sr<sup>2+</sup> charge dimense and the carriers are treated within a Hartree approximation; and the on-site interactions are treated by unrestricted Hartree-Fock. The phase diagram as a function of interaction strength and layer number is determined and predictions are made for optical conductivity experiments. A note worthy nding is that the edges of the heterostructure are generally metallic.

#### I. IN TRODUCTION

\Correlated electron systems" (such as transition metal oxides) are materials in which strong electronelectron or electron-lattice interactions produces behavior incompatible with the standard \density functional plus Migdal-Eliashberg" theory which describes most compounds. The past decade has seen trem endous progress in the physics and materials science of correlated-electron system s. Signi cant im provem ents in crystal and Im grow th, in measurem ent techniques and in theory have led to a much improved understanding of the bulk properties of these materials. An important nding is that correlated electron system s exhibit a multiplicity of interesting phases (superconducting, magnetic, charge and orbitally ordered) along with associated novel excitations. For recent review s, see Ref. 1, or the articles in Ref. 2.

The recent success in treating bulk properties suggests that the time is ripe for a system atic study of the surface and interface properties of correlated electron system s. In addition to its basic in portance as a fundam ental question in m aterials science, correlated electron surface/interface science should provide the necessary scienti c background for study of potential devices exploiting correlated electron properties, because essentially any device must be coupled to the rest of the world via motion of electrons through an interface, and for study of correlated electron nanostructures, because essentially the de ning property of a nanostructure is a high surface to volum e ratio. The fundam ental interest of bulk correlated electron materials lies in the novel phases they exhibit, and we therefore suggest that the fundam ental issue for the nascent eld of \correlated electron surface science" is \ how does the electronic phase at the surface dier from that in the bulk"; in other words, \what is the electronic surface reconstruction."

This question has begun to attract experimental attention. Hesper and co-workers have shown that the [111] surface of K $_3$ C  $_{60}$  di ers from bulk because of charge transfer caused by a polar surface.<sup>3</sup> M atzdorf and collaborators have demonstrated that in the correlated electron system C a<sub>0:9</sub>Sr<sub>0:1</sub>R uO<sub>3</sub> (which exhibits M ott m etalinsulator transition), the surface layers remain m etal-

lic down to a lower temperature than does the bulk system.<sup>4</sup> Izum i and co-workers have fabricated \digital heterostructures" com posed of di erent transition m etal oxides and have dem onstrated changes in electronic phase and other properties depending on the thicknesses of different layers.<sup>5</sup> In an experim entaltour-de-force, 0 htom o, M uller, G razul, and H w ang have dem onstrated the fabrication of atom ically precise digital heterostructures involving a controllable number n of planes of LaT iO  $_3$  (a correlated-electron M ott-insulating m aterial) separated by a controllable numberm of planes of SrT iO  $_3$  (a more conventional band-insulating material) and have measured both the variation of electron density transverse to the planes and the dc transport properties of the heterostructure.<sup>6</sup> T heirwork opens the door to controlled studies both of correlated electron physics in con ned dim ensions and of the behavior of the interface between a correlated system and a uncorrelated one.

M any physics and m aterial science issues arise in considering the behavior of correlated electrons near surfaces and interfaces. A tom ic reconstruction m ay occur, and m ay change the underlying electronic structure. For example, the authors of R ef. 4 argue that a change in tilt angle of the surface RuO<sub>6</sub> octahedra increases the electronic hopping, thereby allowing the m etallic phase to persist to lower T. A lso, as noted e.g. by Hesper and collaborators, a change in structure will lead to changes in M adelung potentials, and to the screening which helps de ne the values of m any-body interaction param eters.<sup>3</sup> \Leakage" of charge across an interface m ay change densities away from the com m ensurate values required for insulating behavior. Substrate induced strain is well known to change the behavior of lm s.<sup>7</sup>

Sorting out the di erent contributions and assessing their e ect on the many-body physics is a form idable task, which will require a sustained experimental and theoretical e ort. The experiment of 0 htom o et al. offers an attractive starting point. In this system, the near lattice m atch (1.5 % di erence in lattice parameter) and chem ical similarity of the two components (LaT iO<sub>3</sub> and SrT iO<sub>3</sub>) suggests that atom ic reconstructions, strain, and renorm alizations of many-body parameters are of lesser importance, so the physical e ects of electronic reconstruction can be isolated and studied. Further, the near Ferm i surface states are derived mainly from the Tidorbitals,<sup>8</sup> and correspond to narrow bands well described by tight-binding theory. However, the orbital degeneracy characteristic of T i provides an interesting set of possible ordered phases.

In this paper we undertake a theoretical analysis of the correlated electron behavior to be expected in latticem atched digital heterostructures of the type created by O htom o et al.<sup>6</sup> W e focus on electrons in the Ti-derived bands, and include the e ects of the long-ranged electric elds arising both from the La atom s and the electronic charge distribution. We treat the extra on-site interactions via a Hartree-Fock interaction. We calculate the electronic phase diagram as a function of on-site interaction parameter and number of La layers and for the relevant phases determ ine the spatial variation of charge, spin and orbital densities. We obtain a complex set of behaviors depending on interaction strength and num ber of La layers. Generally, we nd a crossover length of approximately three unit cells, so that units of six or more LaT iO 3 layers have a central region which exhibits bulklike behavior. The outmost 3 layers on each side are however metallic (in contrast to the insulating behavior of bulk LaT iO 3). For very thin superlattices the ordering patterns di er from bulk. W e calculate optical conductivity spectra and show that this is a revealing probe of the electronic structure.

The rest of this paper is organized as follows: Section II de nes the model, parameter values, and method of study. Section III presents our results for the T = 0phase diagram as a function of interaction strength and num ber of LaT iO 3 layers. Section IV presents our results for the spatial dependence of the charge density in the small U regime where neither spin nor orbital ordering occur and provides, for this simpler case, an overview of the general features of the electronic structure. Section V studies the onset of spin and orbital order as the interaction and layer thickness are increased. Section VI discusses in m ore detail the special case 1 layer. Section V II study the interrelation between the metallic behavior and the subband structure, and a stability under param eter variation. Section V III presents representative results for the optical conductivity, and show show these may be used to elucidate the electronic structure. Finally, section IX presents a sum m ary of our ndings and im portant future directions, and im plications for the general questions of correlated electron surface and interface science, and is designed to be useful to readers uninterested in the details presented in sections II-V III.

#### II. FORMALISM

Both LaT iO<sub>3</sub> and SrT iO<sub>3</sub> crystallize in the simple ABO<sub>3</sub> perovskite structure<sup>9</sup> (m ore precisely, very small distortions occur which we neglect here) and as noted by Ref. 6 the lattice constants of the two m aterials are almost identical;  $a_{LaT iO_3}$  '  $a_{S rT iO_3} = 3.9 A$ , m inim izing structural discontinuities at the interface and presum ably

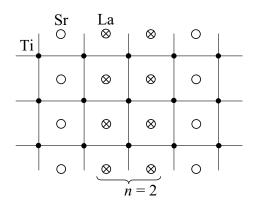


FIG.1: Schematic gure of the model used in the present study. Open and crossed circles show the positions of Sr and La ions. (La layer num bern = 2) The dots show the positions of T i ions. x; y axes are chosen to be parallel to the La plane, and z axis is perpendicular to the plane.

aiding in the growth of high quality digital heterostructures.

In this paper we consider an in nite crystal of SrT iO<sub>3</sub>, into which n adjacent [001] planes of LaT iO<sub>3</sub> have been inserted perpendicular to one of the T i-T i bond directions, as shown in Fig. 1. We choose the z direction to be perpendicular to the LaT iO<sub>3</sub> planes, so the system has a (discrete) translation symmetry in the xy direction.

The relevant electronic orbitals are derived from the Ti  $t_{2g}$ -symmetry d-states, and maybe labeled as  $d_{xy}; d_{xz}; d_{yz}$ . The derived bands  $^{10}$  are to a good approximation given by a nearest neighbor tight binding model with hopping parameter of magnitude t  $^\prime$  0:3 eV and spatial structure given by the Slater-Koster form ula,  $^{11}$  so the  $d_{xy}$  states disperse only in the xy plane etc.

W e take the electrons to hop between T i sites according to a nearest neighbor hopping and to feel a potential de ned by (i) the C oulom b force arising from the extra charge on the La relative to Sr (ii) the C oulom b force arising from the electrons on other T i sites and (iii) onsite H ubbard U and J" interactions with other electrons on the same site. W e take the form of the on-site interactions determ ined by M izokawa et al.<sup>12</sup> and adopt values as discussed below. Thus

$$H_{tot} = \begin{array}{c} X \\ H_{hop} \\ a \end{array} \begin{array}{c} X \\ H_{hop} \\ H \end{array} \begin{array}{c} X \\ H_{Coul} \\ H_{coul} \\ H_{on site} \end{array}$$
(1)

with

$$H_{hop}^{(xy)} = 2t (\cos k_x + \cos k_y) d_{xy;k}^y d_{xy;k}$$
(2)

and sim ilarly for xz; yz. W e have

$$H_{Coul}^{(i)} = V_C (\mathcal{R}_i)_d (\mathcal{R}_i)$$
(3)

with  $_{d}(\mathcal{R}_{i}) = P_{a;} d_{ai}^{y} d_{ai}$  and

Here the  $\Re_i$  are the positions of the Ti<sup>B</sup> sites in the ABO<sub>3</sub> lattice and  $\Re_j^{La}$  label the actual positions of the La ions, which reside on the A sites.

We denote the dielectric function of the host lattice by ". An interesting issue arises here: SrT iO<sub>3</sub> is a nearly ferroelectric material.<sup>13</sup> The static dielectric constant becomes very large at long wavelength and low temperatures, but " is much smaller at high frequencies, room temperature, or short length scales. A loo the polarization P will increase more slow ly at higher elds, and relevant quantity is P = E. In this paper we have chosen " = 15 as a comprom ise between these elses. We discuss the consequences of di erent choices of " in the conclusion. We emphasize that incorporating the ferroelectric tendencies of SrT iO<sub>3</sub> (including the associated lattice distortions) in a more realistic manner is a important question for future research.

Finally, the onsite H is

$$H_{on site}^{(i)} = U_{n_{ai}"n_{ai\#}}^{(i)} + (U_{0}^{0} J)_{n_{ai} n_{bi}}^{(i)} + U_{0}^{0} n_{ai"}n_{bi\#} + J_{ai"}^{(i)} d_{ai"}^{y} d_{bi"} d_{bi\#}^{y} d_{ai\#} + U_{0}^{aeb} d_{ai"}^{y} d_{bi"} d_{ai\#}^{y} d_{bi\#} d_{ai\#} + J_{0}^{aeb} d_{ai"}^{y} d_{bi\#} d_{bi\#} :$$

$$(5)$$

The critical issue is the strength of the on-site repulsion. For de niteness we follow other studies which em – ploy the ratios U<sup>0</sup> = 7U=9 and J = U=9 which are very close to those determ ined by M izokawa.<sup>12</sup> M any workers have used the value U 5-6 eV 18t-20t estimated from high energy spectroscopies.<sup>8</sup> H ow ever, optical conductivity studies of LaT iO<sub>3</sub> and related com pounds such as YT iO<sub>3</sub> nd rather smallgaps, in the range 0.2-1 eV, <sup>14</sup> suggesting U 2:5 eV 8t. In view of this uncertainty we investigate a range U from 6t-20t.

To study the properties of  $H_{tot}$ , Eq. (1), we employ the Hartree-Fock approximation replacing terms such as n<sub>ai</sub> n<sub>bi</sub> by n<sub>ai</sub> hn<sub>bi</sub> i+ hn<sub>ai</sub> in<sub>bi</sub>; orbitally o -diagonal expectation values ( $m_{ai}^{y} d_{bi} i$ ) of the type considered by M izokawa and M ochizuki are stable only in the presence of a GdFeO<sub>3</sub> type distortion which we do not consider. W hile not exact, the approxim ation reveals the correct trends and in particular reveals insulating, ordered states in the parameter regimes where these exist. To implem ent the Hartree-Fock approximation we assume an initial distribution of site, spin and orbital occupancies, obtain the one electron potential by factorizing the interaction terms as described below, compute the band structure, obtain new densities, and iterate until convergence is obtained for som e U-values. M any iterations  $10^3$ ) are required to obtain well-converged solutions, ( essentially because of the delicate balance of particle distributions needed to screen the long range part of the Coulomb interaction.

There are two types of solutions to the one-electron equations: bound states, which decay as jzj! 1, and

continuum states, which do not. A susual in heterostructure problems the bound states give rise to sub-bands, som e of which are partially occupied. The ground state is obtained by lling the lowest sub-bands up to the appropriate chem ical potential (determ ined by charge neutrality); the interaction-related term s in H  $_{\rm C~oul}^{\rm (i)}$  and H  $_{\rm on~site}^{\rm (i)}$ are then recomputed and the procedure is repeated until self-consistency is obtained. Charge neutrality requires that the total density of electrons in the bound-state subbands equals the total density of La ions. However, the interplay between electron-La attraction and electronelectron repulsion leads (in alm ost all of the cases we have studied) to a very weak binding of the highest-lying electron states; indeed for large U the Ferm i level of the partially led sub-bands is only in nitesim ally below the bottom of the continuum bands. A lso in some regions of the phase diagram, there are several locally stable solutions and it is necessary to compare energies, to determ ine the ground state. Between 200 and 3000 iterations were required, with the larger num ber needed either when the Fermilevelad pins the continuum states or when severaldi erent states are very close in energy.

W e now m ention som e speci c details of our solution to the H artree-Fock equations. W e seek solutions which are bound in the z directions; i.e. functions (i;xy) which decay as layer index i ! 1, and which depend on the transverse (xy) coordinates as discussed below.

For each orbital , the functions ' (i;xy) obey a single particle Schodinger equation which we write as

$$t_z a^2 D_{2z} [' (i;xy)] + H_{xy}^{(i)} ' (i;xy) = E' (i;xy):$$
 (6)

Here D<sub>2z</sub>' is the discretized second order derivative  $2'_{i} + '_{i}$  and  $t_{z} = t = 0.3 \text{ eV}$  for = xz;yz′ <sub>i+1</sub> and = 0 for = xy. The term  $H_{xy}^{(i)}$  contains the dispersion in the plane of the layers, as well as term s arising from the long-ranges C oulom b interaction [Eq. (3)]and term s arising from the Hartree-Fock approximation. These terms depend on the on-site interactions and on the charge, spin and orbital density in layer i. A generalm ean-eld state would break translation invariance in the xy plane, in a m anner whose am plitude would depend on layer index i, thereby m ixing the motion in x;y and z directions, leading to a very num erically involved three dimensional self-consistency problem . In order to keep the computations within reasonable bounds and explore wide ranges of param eters, we have in most calculations restricted attention to state which preserve translational invariance in the xy plane. For these states the xy and z m otions decouple, and physical quantities m ay be computed from the solution of a 1d problem combined with an integral over a two-dimensional momentum. We also perform ed som e investigations of states with a twosublattice xy plane structure. In this case, after Fourier transformation on the in-plane coordinate the in-plane Ham iltonian may be written

$$H_{xy}^{(i)} = V_{i} + {}^{i} {}^{m} {}^{p} {}_{j}$$
(7)

with  $V_i$  the part of the potential which is independent of sublattice, <sup>i</sup> the part which alternates between sublattices and "p the in-plane dispersion in the reduced B rillouin zone. The variation of the mixing term <sup>i</sup> with layer requires a separate treatment, lengthening the numerical analysis considerably.

# III. PHASE DIAGRAM

In this section we present and discuss the calculated phase diagram. The geom etry of the heterostructure distinguishes between the xy orbital and the fxz;yzg orbitals. A snoted above, we assume translation invariance in the xy plane. The symmetries which may be broken are therefore spin rotation and orbital rotation (xz and yz) and inversion along with translation invariance in the xy plane. A lso, although it does not have precise meaning except in then ! 1 limit, it is physically sensible to interpret results in terms of z-direction translation symmetry breaking when the spin or orbital density oscillates with respect to the total charge density.

O ur calculated phase diagram is shown in Fig.2. For reasons of com putational convenience in scanning a wide range of param eters, we considered mainly phases with translation invariance in the xy plane, how ever forn = 1 and n = 1 we considered also an xy-plane two sublattice sym m etry breaking. We found in agreem ent with previous calculations<sup>12,15,16,17</sup> that the fully staggered phase is favored at n = 1 , but xy-plane sym m etry broken states could not stabilized in the one layer case. We have not yet studied m ore general sym m etry breakings for intermediate layer num bers, but physical argum ents presented below strongly suggests that these phases only occur for larger num bers of layers (n > 6).

Four phases are found: a small U phase with no broken symmetry, and intermediate U phase with in-plane translation-invariance spin order, but no orbital order, and a large U phase with both spin and orbital order. The lower U transition line varies smoothly with layer number, while the larger U transition is essentially independent of layer number for n > 1. Further, the n = 1intermediate U phase is ferrom agnetic whereas for n > 1the intermediate U phase is antiferrom agnetic. A swill be shown in sections below this behavior can be related to the sub-band structure but the essential reason is that for sm all n the charge density is spread in the z direction, so no layer has a density near 1.

For all n, the low er-U transition is found to be second order. A s U is increased above this value, the m agnetization increases rapidly and the upper transition is strongly rst order. Fig. 3 shows an example of the procedure used to determ ine the location of the phase boundary and the order of the transition. The upper panel of gure 3 displays the energies of several di erent phases. W e identify  $U_{c1}$  as the point where the di erent energies converge (this is m ost easily done from a plot, not show n, of the energy di erences on a expanded scale) and  $U_{c2}$  from

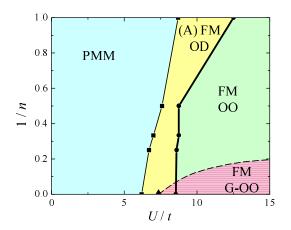


FIG.2: Theoretical ground state phase diagram as a function of the on-site C oulom b interaction U and inverse of the La layer number n. Parameter values are chosen to be U<sup>0</sup> = 7U=9 and J = U=9.  $e^2=("at) = 0.8$  which corresponds to " 15 with a lattice constant a = 3:9 A and transfer intensity t = 0:3 eV. The triangle is the critical U to the (;;) orbital ordering at n = 1 case. The broken line shows the expected phase transition to the (; : ) antiferrom agnetic c

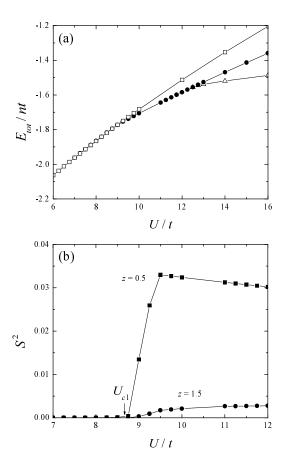


FIG.3: (a) Energy as a function of U (n = 1). Open squares: the spin and orbital-disordered state, lled squares: the spinorder orbital-disorder state, open circles: the spin and orbitalordered state. (b) Square of m agnetization as a function of U in the interm ediate coupling region (n = 1).

the lowest crossing point of the energy curves. That the energies of two qualitatively di erent states cross at U<sub>c2</sub> identi es this as a rst order phase transition, that the energies merge at U<sub>c1</sub> suggests a second order transition. Further evidence is provided by panel (b), which shows, on an expanded scale, the magnetization as a function of U U<sub>c1</sub>, and suggests a continuous decrease to zero.

The comparison to the n = 1 lim it is subtle. In bulk LaT iO  $_3$  exhibits a (;;) type antiferrom agnetic ordering. Theoretical calculations (apparently con med by very recent NMR experiment, and x-ray and neutron di raction experim ents)<sup>18,19</sup> suggest a four sublattice structure which is very close to a (0;0; )-type orbital ordering<sup>20</sup> di ering slightly from the (0;0; ) ordering studied here. Stabilizing the observed state apparently requires a lattice distortion not included in the model. studied here. As U is increased from zero the n ! 1 lim it of the model considered here has a phase transition which we believe to be of second order to an incommensurate antiferrom agnetic state with a wave vector which is an extrem al spanning vector of the Ferm i surfaces of the bands arising from two of the orbitals (say xz; yz) and which turns out to be very close to (0;0; ). (In fact, for reasons of num erical simplicity we studied (0;0;)ordering and found a very weakly rst order transition.) This transition is followed by a strongly rst order transition to one of a degenerate manifold of states characterized by ferrom agnetic spin order and (;; ) orbital order. To maintain continuity with the heterostructure calculations we have also suppressed the (;;) ordering and located the phase boundary to the (m etastable) (0;0; )-orbital spin-ferrom agnetic state. W e believe the (;;)-orbital spin-ferro state we have found is a reasonable surrogate for the actual M ochizuki-Im ada state found in experiment. A lthough this state is favored at n! 1, the physical origin, explained below in more detail, of our inability to stabilize states with broken inplane translation invariance at n = 1 suggests that the (;;) phases only occur for rather thick superlattices. The essential point is that, for n < 6, the solution in the large U lim it consists of several partially lled sub-bands, which have e ectively m in im ized their interaction energy but which gain considerable kinetic energy from motion in the xy plane. Breaking of xy translation symmetry would reduce this kinetic energy gain without much decreasing the already saturated interaction energy while z-direction kinetic energy is quenched by the con ning potential.

The estimate of U = 8t-10t derived from optical measurements on bulk, and from the recent work on the nature of the ordered phase suggests an interesting series of phase transitions may occur as layer thickness is varied.

#### IV. SM ALL U REGION

In this section we present and discuss the results obtained for U < U<sub>c1</sub> where no symmetry breaking is

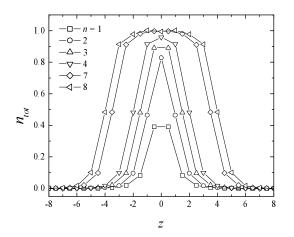


FIG.4:Calculated totalelectron density in the sm all U region (U = 6t). Our results (not shown) for larger U values are alm ost identical.

observed. Although the system geometry implies xy and fxz;yzg orbitals are inequivalent, the occupancies of those orbitals are found to be almost the same; the ratio at the center cite is given by  $(n_{xz} \quad n_{xy})=n_{xz} = 0.023;0.098$  and 0.049 for n = 1;2 and 3, respectively, at U = 6t. Therefore, we mainly focus on the spatial distribution of the total electron density below.

Num erical results for the electron density for several choices of La layer n and U = 6t are shown in Fig. 4. Here we set the origin of z axis at the center of n La layers. E lectron density is sym m etrically distributed around z = 0. The density at the center site rapidly increases with increasing n, and exceeds 0.9 at n = 6. How ever, for this and larger U values, the charge density never exceeds unity, even at the center sites. Fig. 4 shows clearly that for thick layers the length scale over which density vary is about three unit cells, and this number is almost independent of n, and depends som ew hat on " and weakly on U<sup>21</sup>. Thus, at least 6 layers seem to be required before bulk behavior is recovered in the central region. As is well known, SrT iO  $_3$  is close to ferroelectric, and the long wave-length, and linear response dielectric constant becom es about 20000 at the lowest tem perature.<sup>13</sup> The present results involve " at short scales, and are clearly outside the linear response regime. However, tem perature dependent changes in the density pro le should occur and are worth experimental study. Another interesting feature to note is that for all " and U studied the electron and hole distributions at large n are alm ost sym metric at the edge z = n=2;  $n_{tot}(z)$  and  $1 = n_{tot}(n=2 = z)$ fall on alm ost the same line (not shown).

It might be interesting to compare the present numerical results (n = 1;2) with the experimentally observed T i<sup>3+</sup> spatial distributions.<sup>6</sup> The observed T i<sup>3+</sup> decay length of T i<sup>3+</sup> is about 2 nm (5 unit cells) in both n = 1 and 2, which is longer than the present theoretical results (about 3 unit cells). The reported La-ion distribution suggests that the spatial resolution of the EELS m easurem ent is about 0.4 nm (1 unit cell). Inclusion of such e ect m akes the density distribution proles closer to the experim entalones, but the experim ental distributions are still broader than the present theoretical ones. One possibility is La/Sr interdi usion (not considered here). An alternate origin could be a chemical shift of the T i  $t_{2g}$  level. Here we have considered only the long-range C oulomb energy, but an additional contribution arising from the slightly di erent local structure [sm all ionic radius of La<sup>3+</sup> (1.045 A) than that of Sr<sup>4+</sup> (1.13 A)]<sup>22</sup> could bring the La-T id-levels closer to Sr-T id-levels. This e ect has not been included in this study.

#### V. ONSET OF POLARIZATION; LARGER U

This section presents results for large U values, where spin and orbital orderings are observed. The m ain focus is on how the orderings are developed.

Figure 5 (a) and (b) show the electron densities per orbital in the interm ediate coupling regime (U = 8t) with n = 2 where only spin ordering is observed. The di erence between the fxz; yzg and xy occupancy arise only from the symmetry. As a comparison, electron densities per orbital and spin in the m etastable param agnetic state are also shown (crossed squares). From the dierence between the up and down electron occupancy, one can notice that the spin density oscillates around the center site. (although no site is fully polarized) In contrast for n = 1 and 8t < U < 12t, the magnetic state is di erent: the spins align ferrom agnetically. The behavior at n = 1can be attributed to the lower charge density at each site implying low occupancy of each sub-band, so a sm all shift between the up and down electron sub-bands can stabilize the fully polarized state. On the contrary, ferrim agnetic spin ordering at n 2 com es from a delicate balance between the con nem ent potential and on-site Coulomb repulsion.

The electron densities per spin and orbital in the strong coupling regime (U = 10t) are shown in Fig. 5 (c) and (d). The di erence between xz and yz orbital occupancy clearly indicates antiferro-type orbital ordering along the z direction (0;0; ). One can also notice that spin polarization is alm ost com plete. A tiny am ount (less than 1 %) of down spin electrons exist only in the xy orbitals. Note that the orbital ordering in the strong coupling regime is di erent from that expected in the bulk limit where translational symmetry in xy plane would also be broken. In the smalln region, the symmetry is favorable to gain the kinetic energy by two dimensional electron motion.

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In this section, we discuss special features of the n = 1 case. W ithin the Hartree-Fock approximation we have

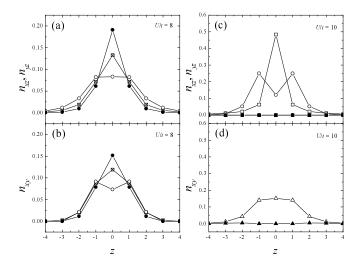


FIG.5: Electron density per spin and orbital in the interm ediate coupling regim e U = 8t (a,b) and the strong coupling regim e U = 10t (c,d) for a heterostructure with two La layers (n = 2). Open and lled symbols show the densities of the up and down spin electrons, respectively. C incles and squares in (a,c) are for the xz and yz, respectively. C rossed squares in (a,b) show the electron density per spin and orbital in a m etastable param agnetic state.

not found any stable states which break xy plane translational invariance. We see from Fig. 4 that at essentially all U the occupancy of any particular orbital state is low. For U > 13t the orbital ordering in the z direction (say xy occupancy to the left of the La layer and yz occupancy to the right), along with the ferrom agnetism e ectively elim inates the on-site interaction contribution to the Hartree-Fock energy, while the fact that the one electron is shared between the two bands means that at each sub-band there is a large kinetic energy gain of order  $\frac{2t}{2} \sin p_F$  per sub-band. W e believe this physics explains why we at n = 1 have been unable to to stabilize a state with two-sublattice in-plane symmetry breaking. In bulk at large U , the kinetic energy is quenched and the (;;) state is stabilized relative to the (0;0;) state by a superexchange of approximately  $2t^2 = (U^0 \quad J)$ 3**1=**U but in the n = 1 superlattice the band energy gain is approximately  $\frac{2t}{2} \sin p_F$ . Indeed this argument suggests that until the band lling becom es close to 1 (which only happens for n > 6) the kinetic energy gain in xy-invariant states is larger than the superexchage energy gained by ordering so that for a range of sm all n (perhaps n < 6) staggered in-plane ordering m ay be neglected.

We do expect the xy-translation invariant states we have found to be unstable to some form of weak incommensurate density wave ordering, because the resulting sub-band structure has a one-dimensional character from the xz and yz sub-bands. However, this ordering is expected to be weak because the residual interactions, not already included in our Hartree-Fock solution, are not strong. For example, in the U > 13t regime, the on-site interactions are fully quenched by

the ferrom agnetic ordering so incom mensurate charge density wave is driven only by the  $2p_F$  component of the long ranged Coulomb interaction, which we estimate from the sub-band charge distribution with half to be  $V_c (2p_F)$ С (2e="a) with C k idth du exp[u<sup>2</sup>(  $=a_{f}^{2}=1+u^{2}$ 0:3-0:4. For the pa-0 ram eters used here  $V_{c}_{2p_{F}}$  $\ln (E_F = T)$  with 0:1. so the instability occurs at a very low T.W e note, how ever, that the precise critical behavior of the second order smallU transition found in our Hartree-Fock approxim ation is likely to be complicated by the additional e ects of  $2p_F$  instabilities in the quasi one dimensional bands. W e leave this interesting issue for future research.

# VII. M ETALLIC EDGE AND STABILITY UNDER PARAMETER VARIATION

The experimental results of 0 htom o et al.<sup>6</sup> show that the interface between the two types of insulators supports a metallic state. From numerical results for thick layer (Fig. 4), one nds a central region where n ' 1, in which one expects bulk-like behavior, and an edge region with n 1, which one might expect to exhibit metallic behavior. In this section, we study the interrelation between the subband structure and metallic behavior. We show that the edge region is responsible for the metallic behavior, and study the dependence of the metallic behavior on parameter changes.

W ithin the Hartree-Fock method we use here, physics of the metallic edge is manifested as follows. There are many bound-state solutions (wave functions decaying as izj is increased away form the heterostructure), whose dispersion in the in-plane direction gives rise to sub-bands. For thin heterostructures, all sub-bands are partially led (implying metallic behavior in the heterostructure plane) whereas for thick heterostructures (in ordered phases), some sub-bands are fully led and some are partly lled. The fully lled sub-bands have z-direction wave functions in plying charge density concentrated in the middle of the heterostructure, whereas the partially led bands have charge concentrated near the edges. The upper panel of Fig. 6 shows the density pro les and the occupancy of partially led bands for the heterostructure with n = 6 and U = t = 10 in a orbitally ordered ferrom agnetic phase. We observe partially led bands corresponding to metallic behavior at the heterostructure edges where the density drops from 1 to 0.

# Two key assumptions underlying the calculations presented so far are the translation invariance of the onsite energy " $_0$ (because in both components of the heterostructure the electronically active ion is octahedrally coordinated T i) and relatively large value for the dielectric constant (to represent the nearly ferroelectric nature of SrT iO<sub>3</sub>). We investigate the sensitivity of this result to changes in these parameters. The low erpanel of F ig. 6 shows the changes in the density pro le and in the oc-

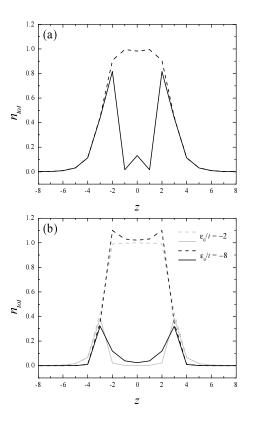


FIG.6: Upper panel: density prole (dashed line) and density in partially occupied bands of heterostructure with n = 6, U = t = 10 and " = 15 calculated in orbitally-ordered ferrom agnetic phase. Lower panel: Density prole (dashed lines) and density in unoccupied bands (light and heavy solid lines) for on-site binding to T i sites in heterostructure (on site energy for T i) between two La planes "0; on site energy for \edge" T i sites (between Sr and La planes) "0=2.

cupancy of partially led bands occurring if the on-site energy is changed for sites near La sites. Here, we have chosen the site energy of those T i sites which sit between two Sr planes to be zero, the energy of a T i site between two La planes to be " $_0 < 0$  and the energy of a T i site between a La plane and a Sr plane to be " $_0=2$ . For " $_0 = 0$  several partially led bands exist, leading to a high density of m etallic electrons. As " $_0$  is decreased, the electronic structure rapidly rearranges so that m ost bands becom e fully led. How ever, even for the largest " $_0$  the geom etry ensures that one electron always remains to be shared between two nearly degenerate bands, one on either side of the heterostructure, so the m etallic behavior remains robust.

W e m ay sim ilarly consider changes occurring as the dielectric constant is varied. F ig. 7 shows the param agnetic phase density pro le occurring as the dielectric constant is varied over a wide range. The m ain e ect is to decrease the tailing of charge density far into the SrT iO<sub>3</sub> layer. How ever, there again remains one electron to be shared between the two edge subbands, the basic phenom enon of partly led bands at the edge is una ected.

Sum marizing, for reasonable parameters we nd that

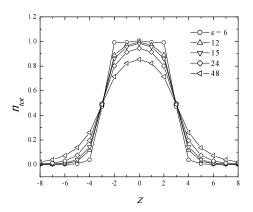


FIG. 7: D ependence of total charge density on dielectric constant calculated for param agnetic phase of 6 layer heterostructure with U=t=10 in param agnetic phase.

there are always partially led bands, corresponding to m etallic behavior at the heterostructure edges. The possibility of m etallic behavior at the edge of a M ott insulator system appears to be con m ed by the experim ental results of O htom o et al.<sup>6</sup> would be interesting study further both experim entally and by m ore sophisticated theoretical m ethods.

#### VIII. OPTICAL CONDUCTIVITY

There are two classes of solutions to the Hartree-Fock equations: bound states, which have wave functions which decay as jcj is increased away from the La layers, and continuum states, extended in all three directions. A lthough the existence of sharply de ned single-particle states at all energies is an artifact of the Hartree-Fock approximation, we expect this qualitative structure to survive in a more sophisticated treatment. Therefore, in this section we use the Hartree-Fock approximation to show how optical conductivity can provide information on the nature and lling of the bound states. We also present a qualitative discussion of the elect of interactions beyond Hartree-Fock.

W e consider electric eld directed perpendicular to the La-planes (parallel to z) and use the Peierls-phase approximation to determ ine the current operator

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$$\hat{J}_{z} = it \qquad \begin{array}{c} x \\ d_{ai}^{y} \\ d_{ai} + \hat{z} \end{array} \qquad h : :: \qquad (8)$$

We then evaluate the usual Kubo formula using the Hartree-Fock eigenstates. Note that in the nearest neighbor tight binding approximation the  $d_{xy}$  states do not couple to z-electric eld, so we will not discuss them in this section.

Figure.8 shows the calculated T = 0 conductivity for the case of one La layer, and two values of U: U = 6t(light curve), for which the system is in the spin and orbital disordered phase, and U = 10t (heavy curve),

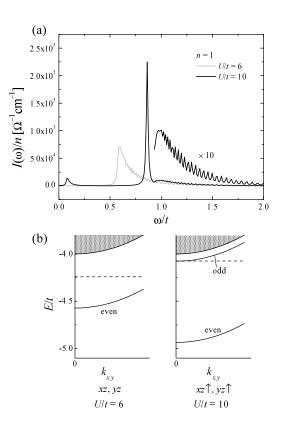


FIG.8: (a) Optical conductivity for n = 1 with U = 6t (sm all U regim e) and 10t (interm ediate U ferror agnetic state). Electric eld E is chosen to be parallel to z. Delta functions are approximated as Lorentzian with the half-maximum half-width 0:1t. (b) Schematic illustrations of sub-band energy structure at U = 6t (left) and U = 10t (right). Shaded areas show the continuum state. Broken lines show the Fermi energy.

for which the system is in the ferrom agnetic, orbitally disordered state.

For U = 6t the xz; yz part of the spectrum (show n in the lower left panel) consists of one four-fold degenerate bound-state sub-band, containing approxim ately 1/6 electron per spin per orbital, as well as em pty continuum bands. The optical spectrum therefore consists of one feature, corresponding to a bound-continuum state transition. The absorption is peaked at the bound state energy, the width re ects the degree of overlap between continuum and bound state energies. The oscillator strength is related to the kinetic energy in the z direction, and is approxim ately 10<sup>4</sup> <sup>1</sup> cm <sup>1</sup>/La. W e expect this spectrum to be very little a ected by correlation e ects beyond Hartree-Fock, because the basic bound state energetics are xed by charge neutrality and Coulom b interaction, and the nal states are continuum states, which are delocalized in space.

A los shown in the upper panel of Fig. 8 is the spectrum corresponding to n = 1 and U = 10t. For these parameters the electronic structure has changed (lower right panel of Fig. 8); there are now two sub-bands; one more strongly bound than in the U = 6t case and holding

m ore electrons (but still only approximately 1/3 lled) and one only very slightly lled band. The calculated

(!) correspondingly exhibits three features, a weak low 0:1t) feature arising from transitions from energy (! the very slightly led bound to the continuum, a sharp higher energy (! 0:9t) feature arising from the inter subband transition (allowed because the lower sub-band is even under z \$ z and the upper is odd) and a ver broad feature from lower bound-continuum transitions The intersubband transition contains about 2/3 of the total oscillator strength; the remainder is mainly in the bound-state to continuum peak. We note that as expected on general grounds, the presence of a bound-state to bound-state transition sharply reduces the weight in the continuum (com pare U = 8t; 10t), essentially because of the requirem ent that the continuum states be orthogonal to both bound states.

W ithin the model we have used the intersubband transition is a delta function, because lifetime e ects have been neglected and the x; y and z direction dispersions decouple, so the 2 sub-bands disperse in the sam e way as  $k_x$  or  $k_y$  is varied. The dispersions decouple because  $w \in$ have adopted a nearest neighbor tight binding model, however this is believed to be reasonably accurate in practice. A potentially more signi cant source of broadening is the \Hubbard U " interaction. Experience from sim plerm odels suggests that for these U -values (of order of the critical value for the bulk system M ott transition) and electron concentration (less than 0.4 electrons per layer, far from the M ott value n = 1) these e ects are not too severe: essentially because the probability of 2 particle collisions scales as n<sup>2</sup>, only a sm all fraction o: the spectral weight will be shifted to an \upper Hubbard band" feature at an energy U, and lifetim e broadening will be rather less than the Ferm i energy, so roughly we expect the peak to rem ain unchanged. These arguments apply also to the other cases we consider below.

We now discuss the n = 2 case. In the smallU param agnetic, orbital disordered case, the electronic spectrum exhibits two bound-state sub-bands; arising from a more strongly bound even parity state and a weakly bound odd parity state. The band structure is very sim ilar to that shown in the right panel of Fig. 8 (b), but without spin polarization. The optical conductivity (not shown) is essentially the same as the U = 10t curve shown in Fig.8. Increasing U to U = 8t leads to a spin ordered (here ferrim agnetic) orbitally disordered state, with four sub-bands and partially occupied] and correspondthree below ingly two bound-state to bound-state transitions (one for each spin) and three bound-state to continuum transitions (the middle one of which is evidently extremely weak).

As a nalexample, we show the optical spectrum and energetics for the spin-ferro orbital-antiferro U = 10tstate. Five bound states now occur, and correspondingly three sharp peaks (recall the optical selection rule allows coupling only from even to odd parity states). Four bound-state-continuum transition should be visible (the

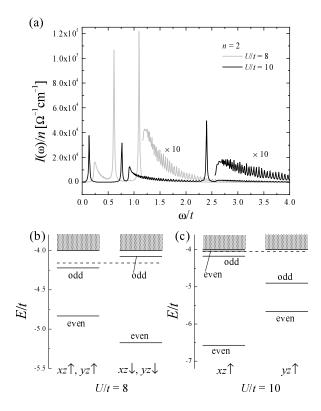


FIG.9: Optical conductivity for n = 2 with U = 8t (interm ediate U ferrim agnetic state) and 10t (large U ferrom agnetic orbital ordered state). Schem atic illustrations of sub-band energy structure at U = 8t (b) and U = 10t (c). Shaded areas show the continuum state. Broken lines are the Ferm ienergy. R em ark: band curvature not show n.

highest-lying xz even parity state is essentially unoccupied) but again all are weak and the low est-lying (arising from the odd  $d_{xz}$  band) is especially weak because the low -lying even-parity continuum states must be orthogonal to the even-parity bound state, which absorbs all the oscillator strength.

To sum marize: the electronic spectrum consists of a num ber of di erent sub-bands (with the detailed structure depending on num ber of La layers and on the nature of the ordering, if any). The optical spectrum for z-polarized light is predicted to consist of relatively sharp peaks, which m ay be assigned to the di erent optically allowed intersubband transitions, along with broad features (often rather weak) associated with transitions from sub-bands to the continuum.

## IX. SUMMARY AND CONCLUSION

In this paper we studied theoretically the phase diagram and electronic properties of a \correlated heterostructure" model involving n layers of a material which in bulk is a Mott insulator, embedded in an innite band insulator. The speci c features of the model we study were chosen to reproduce the LaT iD 3/SrT iD 3 superlattice system studied by O htom o et al., but we hope that our results will shed light also on the more general question of the physics of the interface between a strongly correlated and weakly correlated system s.

A crucial feature of the experim ental LaT iO 3/SrT iO 3 system studied by O htom o et al. is the alm ost perfect lattice match between the two systems. These authors argued that this in plies that the only di erence between the Mott insulating and band insulating regions arises from the dierent charge of the La(3+) and Sr(2+); in particular the crystal structure and atom ic positions are expected to remain relatively constant throughout the heterostructure. Of course, the asymmetry present at the LaT iO 3/SrT iO 3 interface must induce som e changes in atom ic positions: a TiO 6 octahedron is negatively charged, and so if it sits between a Sr plane and a La plane it will be attracted to the latter, and also distorted, because the positively charged Tiwill tend to move in the opposite direction. The experimentally determined Ti-Tidistances shown in Fig. 1 of Ref. 6, along with the distortion in that paper, suggests that the changes in T i-T i distance are negligible. In this circum stance, changes in O position along the Ti-O-Tibond change hoppings only in second order. We therefore neglected these elects and assumed that the electronic hoppings and interaction param eters rem ain invariant across the heterostructure. However, we emphasize that properly accounting for the e ect of atom ic rearrangem ents inevitably present at surface and interface is crucial. W e further note that lattice distortions appear to be in portant in stabilizing the observed bulk state, but may be pinned in a heterostructure. Extending our results to include these e ects is an important open problem .

In the calculation reported here the heterostructure is de ned only by the di erence (+3 vs + 2) of the La and Sr charge. The calculated electronic charge density is found to be controlled mainly by electrostatic e ects (ionic potentials screened by the electronic charge distribution). Results, such as shown in Fig. 4 for U = 6t, are representative of results obtained for a wide range of on-site interaction U.We nd generally that signi cant leakage of charge into the band insulator region occurs. The width of the transition region must depend on the relative strength of the z-direction hoppings and the conning potential. For the parameters studied here, the transition region is about 3 layers (so one needs about 7 La layers to obtain a central region with bulk behavior), and that the n = 1 case is special because the La counterions sit between the Tiplanes. We note, however, that the moderate to large U-values which we study do ensure that even for thick superlattices the charge density on the central layers never becom es greater than unity.

The calculated width is found to be som ewhat less than that found by 0 htom o et al., broadening our distribution by the experimental uncertainty (obtained from the La positions) leads to calculated width about 2/3 of measured ones. W hether the di erence arises because we have overestim ated the con ning potential or for som e other reason such as La/Sr interdi usion remains to be determ ined.

We now turn to our calculated phase diagram shown in Fig. 2. It is expected on general grounds that decreasing the number of La layers will raise the interaction values required for obtaining ordered states. Further, the specic structure of the system of present interest in plies an odd-even alternation. Both of these features are indeed observed in our calculation. Our calculation, in combination with the U-values inferred from optics, suggests that the La/SrT iO 3 system may be in the inter-7t-12t) parameter regime in which one or esting (U m ore phase boundaries may be crossed by varying La layer number. A further point, perhaps especially relevant to systems such as titanates which allow for orbital ordering and orbitally dependent hopping, is that the structural anisotropy intrinsic to the heterostructure m ay favor di erent ordering patterns than those found in bulk. Thus we nd for the thinnest heterostructures di erent phases with more translational invariance than found in bulk. We note, however, that in the Ticase the \edge states" have a quasione-dim ensional character with an incommensurate lling, perhaps favoring incom m ensurate charge, spin or orbital ordering at the edge.

The issue of the transport properties of the heterostructure is an important open question, especially in light of the interesting transport data of Ref. 6. A crucial experimental nding is that metallic conduction is always observed, consistent with our prediction of conducting edge states. However, we do not have a qualitative understanding of the Hall data, because within the Hartee-Fock approximation the Hall resistivity is obtained by adding up the contributions of the di erent sub-bands. The contributions to xy arising from the quasione-dim ensionalxz; yz sub-bands are controlled by weak deviations from the nearest neighbor hopping approximations, which control the mixing between the two bands and the reconstruction of the Ferm i surface of the crossing point. It is di cult to make general statem ents without more detailed band structure inform ation, but som e degree of com pensation is expected.

O ther important issues for future research include study of correlation e ects beyond the Hartree-Fock approximation, inclusion of the coupling between atom ic rearrangements, orbital ordering and electronic hopping parameters, and more sophisticated treatment of the dielectric properties of SrT iD  $_3$ .

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